

# **DMN2170U** N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

#### **Features**

- Low On-Resistance
  - $70m\Omega @V_{GS} = 4.5V$
  - $100m\Omega @V_{GS} = 2.5V$
  - $170m\Omega @V_{GS} = 1.5V$
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2, 3 and 6)
- Qualified to AEC-Q101 Standards for High Reliability
- **ESD Protected Gate**

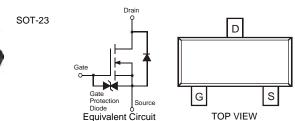




TOP VIEW

#### **Mechanical Data**

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 Marking Information: See Page 3
- Ordering & Date Code Information: See Page 3
- Weight: 0.008 grams (approximate)



**Maximum Ratings**  $@T_A = 25^{\circ}C$  unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	20	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (Note 1)	I <sub>D</sub>	2.3	A
Pulsed Drain Current (Note 4)	I <sub>DM</sub>	8	A

# **Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	PD	600	mW
Thermal Resistance, Junction to Ambient	$R_{ ext{ heta}JA}$	208	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	28	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						·
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.45		1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
		_	50 70 125	70		$V_{GS} = 4.5V, I_D = 3A$
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>			100 170	mΩ	V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 2.3A
	、 <i>/</i>					$V_{GS} = 1.5V, I_D = 0.5A$
Forward Transfer Admittance	Y <sub>fs</sub>	_	6		S	V <sub>DS</sub> =5V, I <sub>D</sub> = 2.4A
Diode Forward Voltage (Note 5)	V <sub>SD</sub>		0.7	0.9	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.05A
DYNAMIC CHARACTERISTICS				_		
Input Capacitance	C <sub>iss</sub>	_	217		pF	
Output Capacitance	Coss		62		pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>		34		pF	

Notes: 1. Device mounted on FR-4 PCB, on minimum recommended, 2oz Copper pad layout.

2. No purposefully added lead. Halogen and Antimony Free.

3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

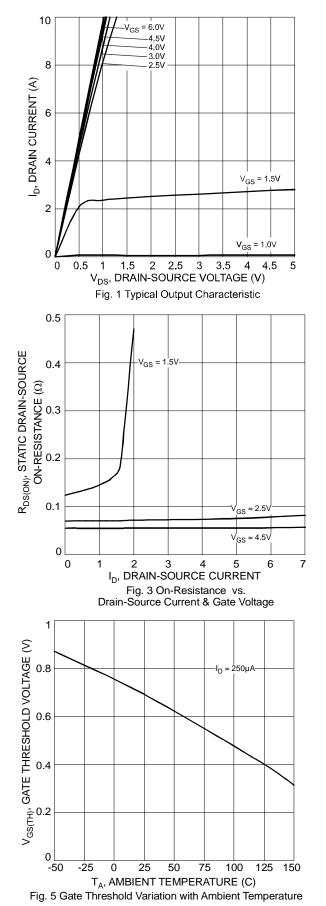
Repetitive rating, pulse width limited by junction temperature.
Short duration pulse test used to minimize self-heating effect.

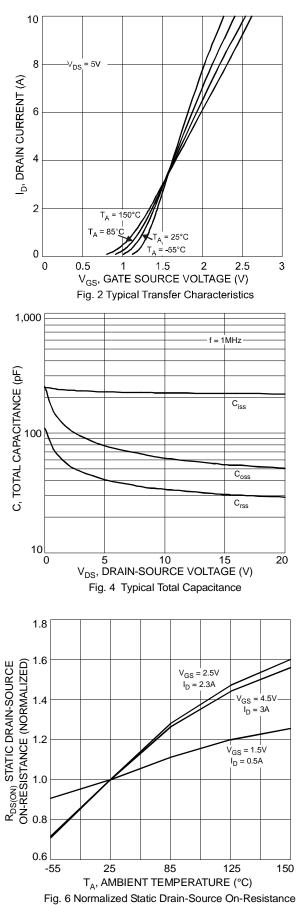
6. Product manufactured with Green Molding Compound and does not contain Halogens or Sb<sub>2</sub>O<sub>3</sub> Fire Retardants.

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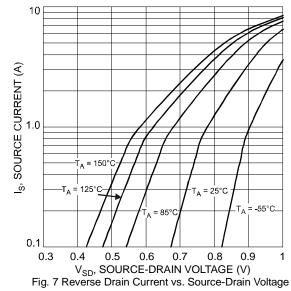


# DMN2170U







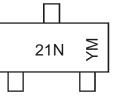


# Ordering Information (Note 7)

Case	Packaging
SOT-23	3000/Tape & Reel
	SOT-23

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**

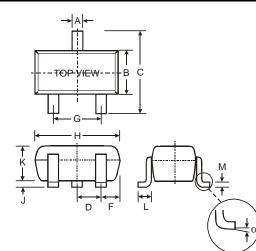


21N = Marking Code YM = Date Code Marking Y = Year ex: U = 2007M = Month ex: 9 = September

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Date	Code	Key (	(If Ap	oplicable)

Year	20	07	20	08	20	09	20	10	20	11	20	12
Code	l	J	١	/	٧	V	2	X	Ŋ	(		<u>Z</u>
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

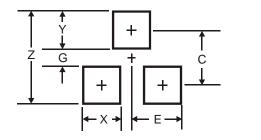
# Package Outline Dimensions



SOT-23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
С	2.30	2.50			
D	0.89	1.03			
F	0.45	0.60			
G	1.78	2.05			
Н	2.80	3.00			
J	0.013	0.10			
K	0.903	1.10			
L	0.45	0.61			
М	0.085	0.180			
α	0°	8°			
All Dir	All Dimensions in mm				



#### Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.4
G	0.7
Х	0.9
Y	1.4
С	2.0
E	0.9

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